East Search Search	L No.	Hits	Text Search		Data Bases
Scarcing	D:170.	11110	(257/18,22,85,94,103,190,200,201).CCL		USPAT; EPO; JPO
IS&R	Lı	2802	S.	7/15/02 14:45	
ISCIN			algainnasp algainasnp algainpasn		USPAT; EPO; JPO
BRS	L5	3	gaalinnasp gaalinasnp gaalinpasn	7/15/02 15:26	
Ditto					USPAT; EPO; JPO
BRS	L8	53	1 and gan adj substrate	7/15/02 15:27	
			gaalinnasp gaalinasnp gaalinpasn		USPAT; EPO; JPO
BRS	L9	19	inalganasp inalgaasnp inalgapasn	7/15/02 15:18	
DRO	 				USPAT; EPO; JPO
BRS	L10	11	9 and @ay<2000	7/15/02 15:27	Derwent; IBM TDI
Ditto	1		algainnasp algainasnp algainpasn		USPAT; EPO; JPO
BRS	L11	2910	gaalinnasp gaalinasnp gaalinpasn	7/15/02 15:26	Derwent; IBM TDI
					USPAT; EPO; JPO
BRS	L12	64	11 and gan adj substrate	7/15/02 15:27	Derwent; IBM TDI
	1	T			USPAT; EPO; JPO
BRS	L13	32	12 and @ay<2000	7/15/02 15:27	Derwent; IBM TDI

Search Resul

Search Result		OLD THE SECRETARISM	PRIOR CONTRACTOR CONTR	Cl/Sub	Cl/Sub	Inventor
USPAT	Date	Page	Title	Chan	20.130.000W	THI CHOOLES
US 20010048114			SEMICONDUCTOR SUBSTRATE		257/627; 257/95;	MODITA ETCHO1
A1	20011206	10	AND SEMICONDUCTOR DEVICE	257/103	372/43	MORITA, ETSUO et al.
					257/201; 257/613;	
US 6359292 B1	20020319		Delitionidaetor right emitting	257/103	257/96	Sugawara, Hideto et al.
			Method for growing nitride compound			L
US 6339014 B1	20020115	9	semiconductor	438/503	257/103; 438/509	Ishida, Masahiro et al.
US 6191439 B1	20010220	10	Semiconductor light emitting device	257/103	257/95; 257/97	Sugawara, Hideto
			III-V aresenide-nitride semiconductor		257/18; 257/184;	l .
US 5689123 A	19971118	21	materials and devices	257/190	257/201; 257/22	Major, Jo S. et al.
US 20010008656	***************************************	-	NITRIDE AND METHOD OF			TISCHLER, MICHAEL A.
A1	20010719	11	MAKING SAME	428/34.1	428/64.1	et al.
711	200101		Gallium nitride group semiconductor			
US 6370176 B1	20020409	13	laser device and optical pickup apparatus	372/45		Okumura, Toshiyuki
03 03/01/0 151	20020102		Method for manufacturing gallium			
US 6121121 A	20000919	5	nitride compound semiconductor	438/481	438/341; 438/479	Koide, Norikatsu
03 0121121 A	20000717		gallium nitride group compound		204/192.35;	
US 5811319 A	19980922	12	semiconductors	438/46	438/47; 438/604	Koike, Masayoshi et al.
US 3811319 A	19980922	- 12	with an improved GaN system double			
110 5742629 A	19980421	1 12	heterostructure	372/45	257/77	Fujii, Hiroaki
US 5742628 A	19900421	12	Method of making a single crystals		117/1; 117/90;	
110 5 6 5 0 1 5 0 A	19971021	10	Ga*N article	117/97	117/915; 438/507	Tischler, Michael A. et al.
US 5679152 A	199/1021	10	Compound semicondutor light-emitting			
	19950711	16	device	372/45	257/77; 372/44	Hatano, Ako et al.
US 5432808 A	19950/11	10	device	1		
	 			<u> </u>		
		L	l			

L Number	Hits	Search Text	DB	Time stamp
1	2802	(257/18,22,85,94,103,190,200,201).CCLS.	USPAT;	2002/07/15 14:45
-	2002	(30,720,720,720,720,720,720,720,720,720,72	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
. 1			IBM_TDB	
5	3	algainnasp algainasnp algainpasn	USPAT;	2002/07/15 14:53
		gaalinnasp gaalinasnp gaalinpasn	US-PGPUB;	
]		inalganasp inalgaasnp inalgapasn	EPO; JPO;	
		alinganasp alingaasnp alingapasn	DERWENT;	
		gainalnasp gainalasnp gainalpasn	IBM_TDB	
•		ingaalnasp ingaalasnp ingaalpasn		
8	53	((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/15 15:17
		and gan adj substrate	US-PGPUB;	!
			EPO; JPO;	
			DERWENT;]
			IBM_TDB	2002/07/15 15:18
9	19	(((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/15 15:16
		and gan adj substrate) and (algainnasp	US-PGPUB;	
		algainasnp algainpasn gaalinnasp	EPO; JPO;	
		gaalinasnp gaalinpasn inalganasp	DERWENT;	
		inalgaasnp inalgapasn alinganasp	IBM_TDB	
		alingaasnp alingapasn gainalnasp		
		gainalasnp gainalpasn ingaalnasp		
		ingaalasnp ingaalpasn algainnas algainasn		
		algainasn gaalinasp gaalinasp gaalinpas		<u> </u>
		inalganp inalganp inalgann alinganasp		
		alingaasnp alingapasn gainalnasp		
		gainalasnp gainalpasn ingaalnasp ingaalnp ingaalpn algainn gaalinn gainaln inalgan		
		algainas gaalinas inalgaas algainp gaalinp		
	11	inalgap) ((((257/18,22,85,94,103,190,200,201).CCLS.)	USPAT;	2002/07/15 15:18
10	11	and gan adj substrate) and (algainnasp	US-PGPUB;	
		algainasnp algainpasn gaalinnasp	EPO; JPO;	
		gaalinashp gaalinpash gaalimasp	DERWENT;	
		inalgaasnp inalgapasn alinganasp	IBM TDB	1
		alingaasnp alingapasn gainalnasp	_	
		gainalasnp gainalpasn ingaalnasp		
		ingaalasnp ingaalpasn algainnas algainasn		
		algainasn gaalinasp gaalinasp gaalinpas		
		inalganp inalganp alinganasp		
		alingaasno alingapasn gainalnasp		
		gainalasno gainalpasn ingaalnasp ingaalno		
1		lingaalon algainn gaalinn gainaln inalgan		
		algainas gaalinas inalgaas algainp gaalinp		
	L	inalgan)) and @ay<2000		